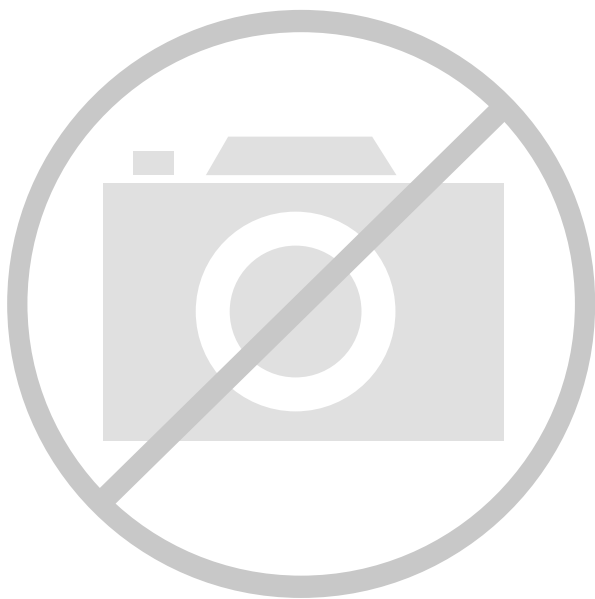




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	252
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1afs1500-2fg676i

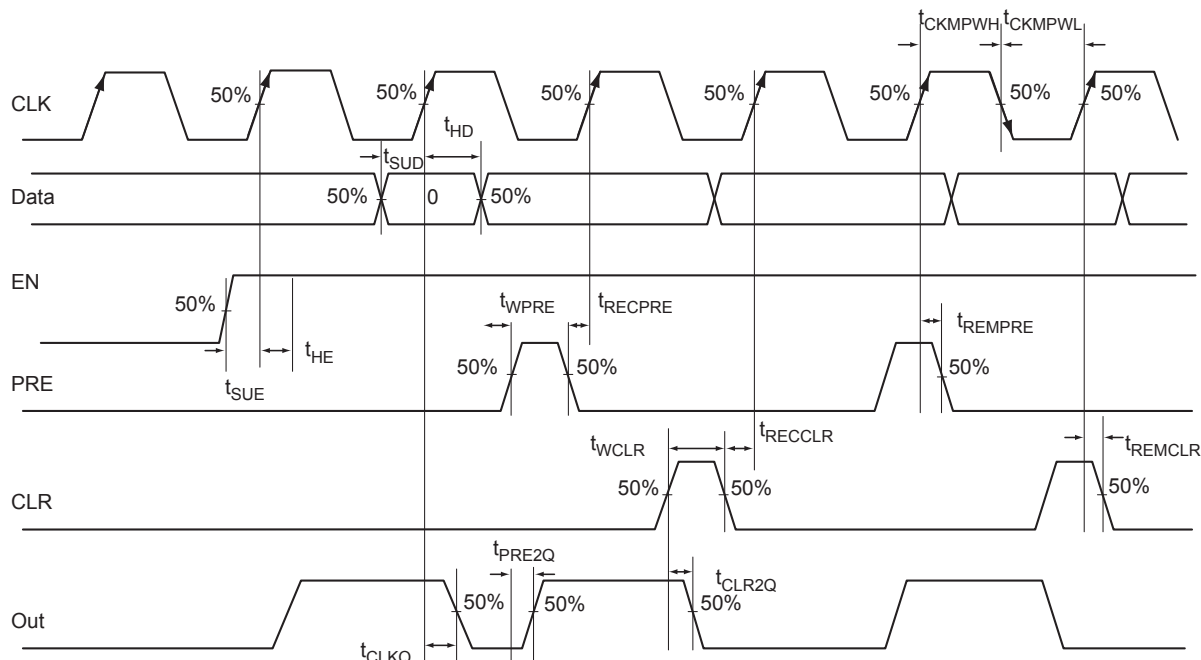


Figure 2-6 • Sequential Timing Model and Waveforms

Sequential Timing Characteristics

Table 2-2 • Register Delays

Commercial Temperature Range Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.55	0.63	0.74	ns
t_{SUD}	Data Setup Time for the Core Register	0.43	0.49	0.57	ns
t_{HD}	Data Hold Time for the Core Register	0.00	0.00	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.45	0.52	0.61	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	0.00	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.40	0.45	0.53	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.40	0.45	0.53	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	0.00	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.22	0.25	0.30	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	0.00	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.22	0.25	0.30	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.22	0.25	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.22	0.25	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.32	0.37	0.43	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.36	0.41	0.48	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Crystal Oscillator

The Crystal Oscillator (XTLOSC) is source that generates the clock from an external crystal. The output of XTLOSC CLKOUT signal can be selected as an input to the PLL. Refer to the ["Clock Conditioning Circuits"](#) section for more details. The XTLOSC can operate in normal operations and Standby mode (RTC is running and 1.5 V is not present).

In normal operation, the internal FPGA_EN signal is '1' as long as 1.5 V is present for VCC. As such, the internal enable signal, XTL_EN, for Crystal Oscillator is enabled since FPGA_EN is asserted. The XTL_MODE has the option of using MODE or RTC_MODE, depending on SELMODE.

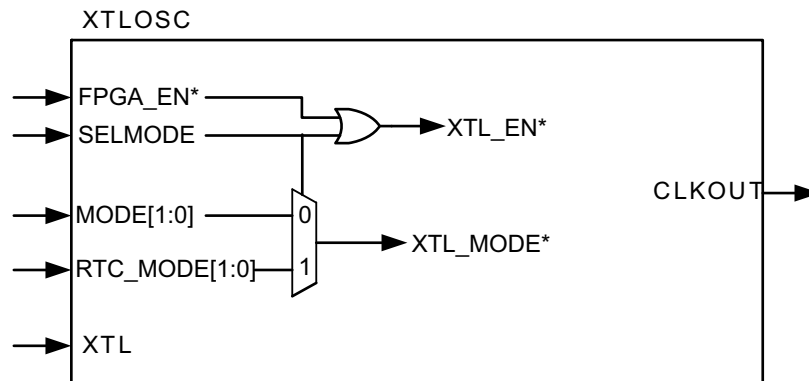
During Standby, 1.5 V is not available, as such, and FPGA_EN is '0'. SELMODE must be asserted in order for XTL_EN to be enabled; hence XTL_MODE relies on RTC_MODE. SELMODE and RTC_MODE must be connected to RTCXTLSEL and RTCXTLMODE from the AB respectively for correct operation during Standby (refer to the ["Real-Time Counter System"](#) section on page 2-31 for a detailed description).

The Crystal Oscillator can be configured in one of four modes:

- RC network, 32 KHz to 4 MHz
- Low gain, 32 to 200 KHz
- Medium gain, 0.20 to 2.0 MHz
- High gain, 2.0 to 20.0 MHz

In RC network mode, the XTAL1 pin is connected to an RC circuit, as shown in [Figure 2-16 on page 2-18](#). The XTAL2 pin should be left floating. The RC value can be chosen based on [Figure 2-18](#) for any desired frequency between 32 KHz and 4 MHz. The RC network mode can also accommodate an external clock source on XTAL1 instead of an RC circuit.

In Low gain, Medium gain, and High gain, an external crystal component or ceramic resonator can be added onto XTAL1 and XTAL2, as shown in [Figure 2-16 on page 2-18](#). In the case where the Crystal Oscillator block is not used, the XTAL1 pin should be connected to GND and the XTAL2 pin should be left floating.



Note: *Internal signal—does not exist in macro.

Figure 2-17 • XTLOSC Macro

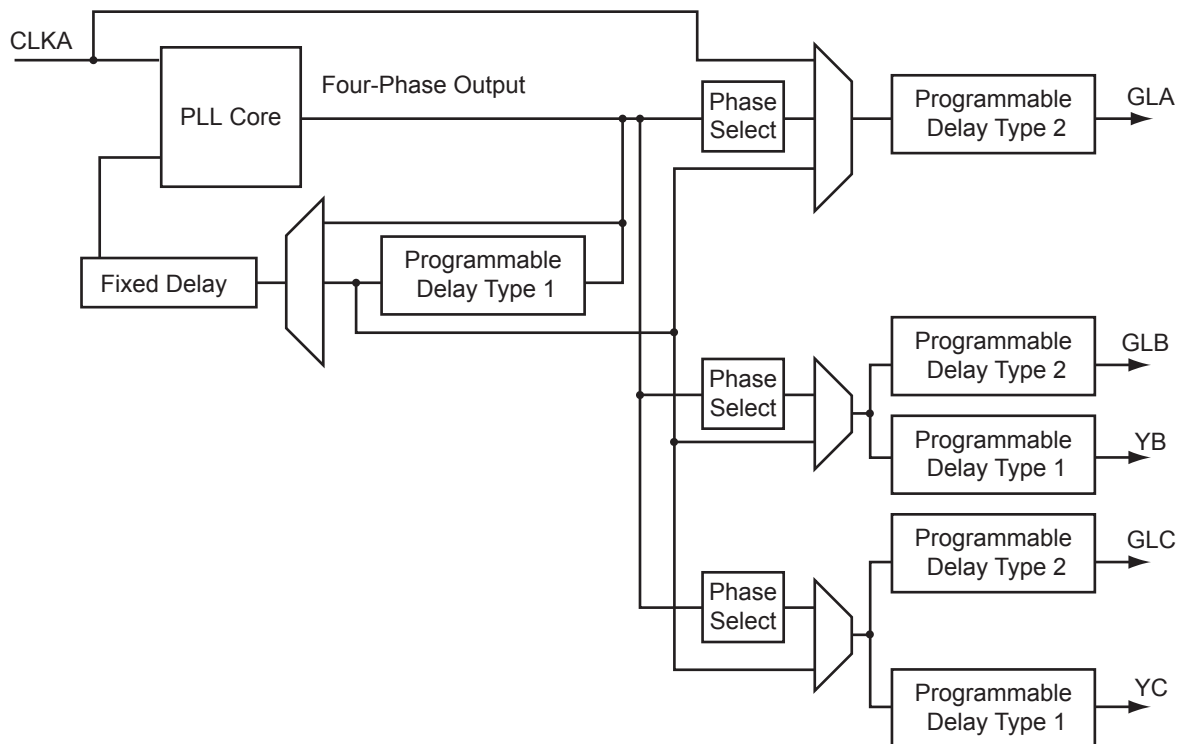
CCC Physical Implementation

The CCC circuit is composed of the following (Figure 2-23):

- PLL core
- 3 phase selectors
- 6 programmable delays and 1 fixed delay
- 5 programmable frequency dividers that provide frequency multiplication/division (not shown in Figure 2-23 because they are automatically configured based on the user's required frequencies)
- 1 dynamic shift register that provides CCC dynamic reconfiguration capability (not shown)

CCC Programming

The CCC block is fully configurable. It is configured via static flash configuration bits in the array, set by the user in the programming bitstream, or configured through an asynchronous dedicated shift register, dynamically accessible from inside the Fusion device. The dedicated shift register permits changes of parameters such as PLL divide ratios and delays during device operation. This latter mode allows the user to dynamically reconfigure the PLL without the need for core programming. The register file is accessed through a simple serial interface.



Note: Clock divider and multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.

Figure 2-23 • PLL Block

Access to the FB is controlled by the BUSY signal. The BUSY output is synchronous to the CLK signal. FB operations are only accepted in cycles where BUSY is logic 0.

Write Operation

Write operations are initiated with the assertion of the WEN signal. Figure 2-35 on page 2-45 illustrates the multiple Write operations.

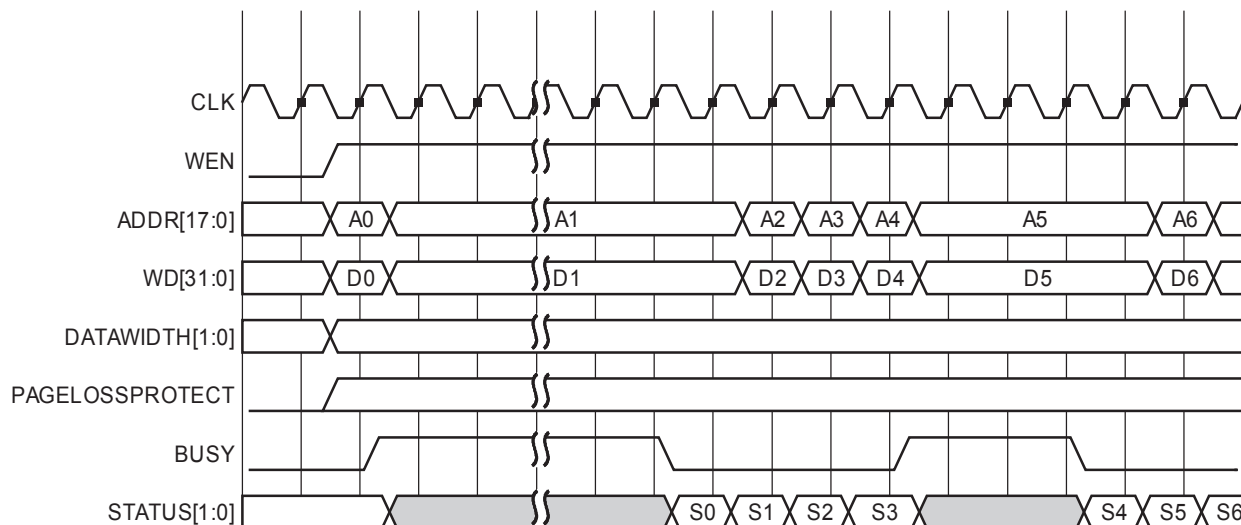


Figure 2-35 • FB Write Waveform

When a Write operation is initiated to a page that is currently not in the Page Buffer, the FB control logic will issue a BUSY signal to the user interface while the page is loaded from the FB Array into the Page Buffer. A Copy Page operation takes no less than 55 cycles and could take more if a Write or Unprotect Page operation is started while the NVM is busy pre-fetching a block. The basic operation is to read a block from the array into the block register (5 cycles) and then write the block register to the page buffer (1 cycle) and if necessary, when the copy is complete, reading the block being written from the page buffer into the block buffer (1 cycle). A page contains 9 blocks, so 9 blocks multiplied by 6 cycles to read/write each block, plus 1 is 55 cycles total. Subsequent writes to the same block of the page will incur no busy cycles. A write to another block in the page will assert BUSY for four cycles (five cycles when PIPE is asserted), to allow the data to be written to the Page Buffer and have the current block loaded into the Block Buffer.

Write operations are considered successful as long as the STATUS output is '00'. A non-zero STATUS indicates that an error was detected during the operation and the write was not performed. Note that the STATUS output is "sticky"; it is unchanged until another operation is started.

Only one word can be written at a time. Write word width is controlled by the DATAWIDTH bus. Users are responsible for keeping track of the contents of the Page Buffer and when to program it to the array. Just like a regular RAM, writing to random addresses is possible. Users can write into the Page Buffer in any order but will incur additional BUSY cycles. It is not necessary to modify the entire Page Buffer before saving it to nonvolatile memory.

Write errors include the following:

1. Attempting to write a page that is Overwrite Protected (STATUS = '01'). The write is not performed.
2. Attempting to write to a page that is not in the Page Buffer when Page Loss Protection is enabled (STATUS = '11'). The write is not performed.

Timing Characteristics

Table 2-31 • RAM4K9

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BL hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Table 2-32 • RAM512X18

 Commercial Temperature Range Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.09	0.10	0.12	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	0.08	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}^1	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Analog-to-Digital Converter Block

At the heart of the Fusion analog system is a programmable Successive Approximation Register (SAR) ADC. The ADC can support 8-, 10-, or 12-bit modes of operation. In 12-bit mode, the ADC can resolve 500 kcps. All results are MSB-justified in the ADC. The input to the ADC is a large 32:1 analog input multiplexer. A simplified block diagram of the Analog Quads, analog input multiplexer, and ADC is shown in Figure 2-79. The ADC offers multiple self-calibrating modes to ensure consistent high performance both at power-up and during runtime.

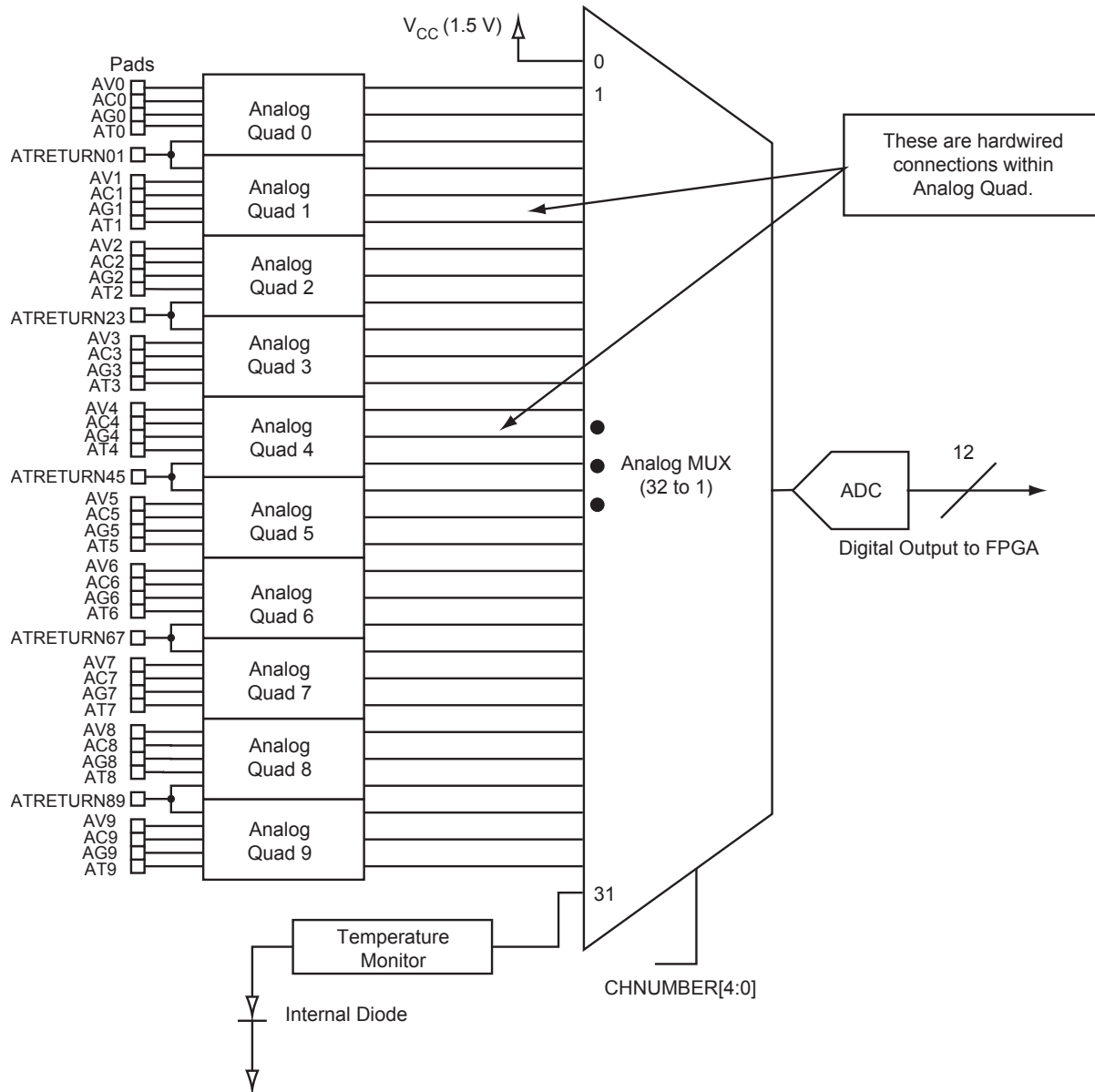


Figure 2-79 • ADC Block Diagram

Table 2-40 • Analog MUX Channels (continued)

Analog MUX Channel	Signal	Analog Quad Number
16	AV5	Analog Quad 5
17	AC5	
18	AT5	
19	AV6	Analog Quad 6
20	AC6	
21	AT6	
22	AV7	Analog Quad 7
23	AC7	
24	AT7	
25	AV8	Analog Quad 8
26	AC8	
27	AT8	
28	AV9	Analog Quad 9
29	AC9	
30	AT9	
31	Internal temperature monitor	

The ADC can be powered down independently of the FPGA core, as an additional control or for power-saving considerations, via the PWRDWN pin of the Analog Block. The PWRDWN pin controls only the comparators in the ADC.

ADC Modes

The Fusion ADC can be configured to operate in 8-, 10-, or 12-bit modes, power-down after conversion, and dynamic calibration. This is controlled by MODE[3:0], as defined in [Table 2-41 on page 2-106](#).

The output of the ADC is the RESULT[11:0] signal. In 8-bit mode, the Most Significant 8 Bits RESULT[11:4] are used as the ADC value and the Least Significant 4 Bits RESULT[3:0] are logical '0's. In 10-bit mode, RESULT[11:2] are used the ADC value and RESULT[1:0] are logical 0s.

Table 2-41 • Mode Bits Function

Name	Bits	Function
MODE	3	0 – Internal calibration after every conversion; two ADCCLK cycles are used after the conversion. 1 – No calibration after every conversion
MODE	2	0 – Power-down after conversion 1 – No Power-down after conversion
MODE	1:0	00 – 10-bit 01 – 12-bit 10 – 8-bit 11 – Unused

Refer to [Table 2-46 on page 2-109](#) and the "Acquisition Time or Sample Time Control" section on [page 2-107](#)

$$t_{\text{sample}} = (2 + \text{STC}) \times t_{\text{ADCCLK}}$$

EQ 20

STC: Sample Time Control value (0–255)

t_{SAMPLE} is the sample time

Table 2-46 • STC Bits Function

Name	Bits	Function
STC	[7:0]	Sample time control

Sample time is computed based on the period of ADCCLK.

Distribution Phase

The second phase is called the distribution phase. During distribution phase, the ADC computes the equivalent digital value from the value stored in the input capacitor. In this phase, the output signal SAMPLE goes back to '0', indicating the sample is completed; but the BUSY signal remains '1', indicating the ADC is still busy for distribution. The distribution time depends strictly on the number of bits. If the ADC is configured as a 10-bit ADC, then 10 ADCCLK cycles are needed. [EQ 8](#) describes the distribution time.

$$t_{\text{distrib}} = N \times t_{\text{ADCCLK}}$$

EQ 21

N: Number of bits

Post-Calibration Phase

The last phase is the post-calibration phase. This is an optional phase. The post-calibration phase takes two ADCCLK cycles. The output BUSY signal will remain '1' until the post-calibration phase is completed. If the post-calibration phase is skipped, then the BUSY signal goes to '0' after distribution phase. As soon as BUSY signal goes to '0', the DATAVALID signal goes to '1', indicating the digital result is available on the RESULT output signals. DATAVALID will remain '1' until the next ADCSTART is asserted. Microsemi recommends enabling post-calibration to compensate for drift and temperature-dependent effects. This ensures that the ADC remains consistent over time and with temperature. The post-calibration phase is enabled by bit 3 of the Mode register. [EQ 9](#) describes the post-calibration time.

$$t_{\text{post-cal}} = \text{MODE}[3] \times (2 \times t_{\text{ADCCLK}})$$

EQ 22

MODE[3]: Bit 3 of the Mode register, described in [Table 2-41 on page 2-106](#).

The calculation for the conversion time for the ADC is summarized in [EQ 23](#).

$$t_{\text{conv}} = t_{\text{sync_read}} + t_{\text{sample}} + t_{\text{distrib}} + t_{\text{post-cal}} + t_{\text{sync_write}}$$

EQ 23

t_{conv} : conversion time

$t_{\text{sync_read}}$: maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .

t_{sample} : Sample time

t_{distrib} : Distribution time

$t_{\text{post-cal}}$: Post-calibration time

$t_{\text{sync_write}}$: Maximum time for a signal to synchronize with SYSCLK. For calculation purposes, the worst case is a period of SYSCLK, t_{SYSCLK} .

Analog System Characteristics

Table 2-49 • Analog Channel Specifications
Commercial Temperature Range Conditions, $T_J = 85^\circ\text{C}$ (unless noted otherwise),
Typical: $V_{CC33A} = 3.3\text{ V}$, $V_{CC} = 1.5\text{ V}$

Parameter	Description	Condition	Min.	Typ.	Max.	Units
Voltage Monitor Using Analog Pads AV, AC and AT (using prescaler)						
	Input Voltage (Prescaler)	Refer to Table 3-2 on page 3-3				
VINAP	Uncalibrated Gain and Offset Errors	Refer to Table 2-51 on page 2-122				
	Calibrated Gain and Offset Errors	Refer to Table 2-52 on page 2-123				
	Bandwidth ¹				100	KHz
	Input Resistance	Refer to Table 3-3 on page 3-4				
	Scaling Factor	Prescaler modes (Table 2-57 on page 2-130)				
	Sample Time		10			μs
Current Monitor Using Analog Pads AV and AC						
VRSM ¹	Maximum Differential Input Voltage				VAREF / 10	mV
	Resolution	Refer to "Current Monitor" section				
	Common Mode Range				- 10.5 to +12	V
CMRR	Common Mode Rejection Ratio	DC – 1 KHz		60		dB
		1 KHz - 10 KHz		50		dB
		> 10 KHz		30		dB
t_{CMSHI}	Strobe High time		ADC conv. time		200	μs
t_{CMSHI}	Strobe Low time		5			μs
t_{CMSHI}	Settling time		0.02			μs
	Accuracy	Input differential voltage > 50 mV			-2 – (0.05 x VRSM) to +2 + (0.05 x VRSM)	mV

Notes:

1. VRSM is the maximum voltage drop across the current sense resistor.
2. Analog inputs used as digital inputs can tolerate the same voltage limits as the corresponding analog pad. There is no reliability concern on digital inputs as long as VIND does not exceed these limits.
3. VIND is limited to $V_{CC33A} + 0.2$ to allow reaching 10 MHz input frequency.
4. An averaging of 1,024 samples (LPF setting in Analog System Builder) is required and the maximum capacitance allowed across the AT pins is 500 pF.
5. The temperature offset is a fixed positive value.
6. The high current mode has a maximum power limit of 20 mW. Appropriate current limit resistors must be used, based on voltage on the pad.
7. When using SmartGen Analog System Builder, CalibIP is required to obtain specified offset. For further details on CalibIP, refer to the "Temperature, Voltage, and Current Calibration in Fusion FPGAs" chapter of the [Fusion FPGA Fabric User Guide](#).

For Fusion devices requiring Level 3 and/or Level 4 compliance, the board drivers connected to Fusion I/Os need to have 10 k Ω (or lower) output drive resistance at hot insertion, and 1 k Ω (or lower) output drive resistance at hot removal. This is the resistance of the transmitter sending a signal to the Fusion I/O, and no additional resistance is needed on the board. If that cannot be assured, three levels of staging can be used to meet Level 3 and/or Level 4 compliance. Cards with two levels of staging should have the following sequence:

1. Grounds
2. Powers, I/Os, other pins

Cold-Sparing Support

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

Pro I/O banks and standard I/O banks fully support cold-sparing.

For Pro I/O banks, standards such as PCI that require I/O clamp diodes, can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

For Advanced I/O banks, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each advanced I/O pin to 0 V.

If Standard I/O banks are used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the standard I/O buffers do not have built-in I/O clamp diodes.

If a resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitor is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

I/O cold-sparing may add additional current if the pin is configured with either a pull-up or pull down resistor and driven in the opposite direction. A small static current is induced on each IO pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Please refer to [Table 2-95 on page 2-169](#), [Table 2-96 on page 2-169](#), and [Table 2-97 on page 2-171](#) for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTTL 3.3 V input pin is configured with a weak Pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven low. For an LVTTTL 3.3 V, pull-up resistor is ~45 k Ω and the resulting current is equal to $3.3 \text{ V} / 45 \text{ k}\Omega = 73 \text{ }\mu\text{A}$ for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven high. Avoiding this current can be done by driving the input low when a weak pull-down resistor is used, and driving it high when a weak pull-up resistor is used.

In Active and Static modes, this current draw can occur in the following cases:

- Input buffers with pull-up, driven low
- Input buffers with pull-down, driven high
- Bidirectional buffers with pull-up, driven low
- Bidirectional buffers with pull-down, driven high
- Output buffers with pull-up, driven low
- Output buffers with pull-down, driven high
- Tristate buffers with pull-up, driven low
- Tristate buffers with pull-down, driven high

Electrostatic Discharge (ESD) Protection

Fusion devices are tested per JEDEC Standard JESD22-A114-B.

Fusion devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the Off state, except when transient voltage is significantly above VCCI or below GND levels.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to [Table 2-75](#) and [Table 2-76 on page 2-143](#) for more information about I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

Table 2-75 • Fusion Standard and Advanced I/O – Hot-Swap and 5 V Input Tolerance Capabilities

I/O Assignment	Clamp Diode		Hot Insertion		5 V Input Tolerance ¹		Input Buffer	Output Buffer
	Standard I/O	Advanced I/O	Standard I/O	Advanced I/O	Standard I/O	Advanced I/O		
3.3 V LVTTTL/LVCMOS	No	Yes	Yes	No	Yes ¹	Yes ¹	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	N/A	Yes	N/A	No	N/A	Yes ¹	Enabled/Disabled	
LVCMOS 2.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V	N/A	Yes	N/A	No	N/A	Yes ²	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
Differential, LVDS/BLVDS/M-LVDS/ LVPECL ³	N/A	Yes	N/A	No	N/A	No	Enabled/Disabled	

Notes:

1. Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.
2. Can be implemented with an external resistor and an internal clamp diode.
3. Bidirectional LVPECL buffers are not supported. I/Os can be configured as either input buffers or output buffers.

Table 2-76 • Fusion Pro I/O – Hot-Swap and 5 V Input Tolerance Capabilities

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTTL/LVCMOS	No	Yes	Yes ¹	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	Yes	No	Yes ¹	Enabled/Disabled	
LVCMOS 2.5 V ³	No	Yes	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V ³	Yes	No	Yes ²	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
Voltage-Referenced Input Buffer	No	Yes	No	Enabled/Disabled	
Differential, LVDS/BLVDS/M-LVDS/LVPECL ⁴	No	Yes	No	Enabled/Disabled	

Notes:

1. Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.
2. Can be implemented with an external resistor and an internal clamp diode.
3. In the [SmartGen](#), [FlashROM](#), [Flash Memory System Builder](#), and [Analog System Builder User Guide](#), select the LVCMOS5 macro for the LVCMOS 2.5 V / 5.0 V I/O standard or the LVCMOS25 macro for the LVCMOS 2.5 V I/O standard.
4. Bidirectional LVPECL buffers are not supported. I/Os can be configured as either input buffers or output buffers.

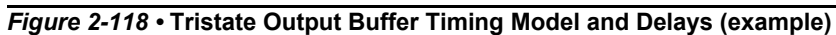


Table 2-98 • I/O Short Currents IOSH/IOSL

	Drive Strength	IOSH (mA)*	IOSL (mA)*
Applicable to Pro I/O Banks			
3.3 V LVTTTL / 3.3 V LVCMOS	4 mA	25	27
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
2.5 V LVCMOS	4 mA	16	18
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
Applicable to Advanced I/O Banks			
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181

Note: * $T_J = 100^{\circ}\text{C}$

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-110 • Minimum and Maximum DC Input and Output Levels

2.5 V LVCMOS	V _{IL}		V _{IH}		V _{OL}	V _{OH}	I _{OL}	I _{OH}	I _{OSL}	I _{OSH}	I _{IL} ¹	I _{IH} ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
Applicable to Pro I/O Banks												
4 mA	−0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
8 mA	−0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10
12 mA	−0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10
16 mA	−0.3	0.7	1.7	3.6	0.7	1.7	16	16	87	83	10	10
24 mA	−0.3	0.7	1.7	3.6	0.7	1.7	24	24	124	169	10	10
Applicable to Advanced I/O Banks												
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	18	16	10	10
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	18	16	10	10
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	37	32	10	10
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	37	32	10	10
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	74	65	10	10
16 mA	−0.3	0.7	1.7	2.7	0.7	1.7	16	16	87	83	10	10
24 mA	−0.3	0.7	1.7	2.7	0.7	1.7	24	24	124	169	10	10
Applicable to Standard I/O Banks												
2 mA	−0.3	0.7	1.7	3.6	0.7	1.7	2	2	18	16	10	10
4 mA	−0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
6 mA	−0.3	0.7	1.7	3.6	0.7	1.7	6	6	37	32	10	10
8 mA	−0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

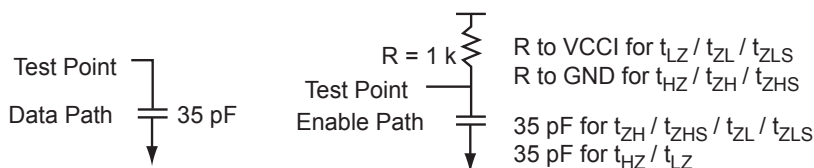


Figure 2-120 • AC Loading

Table 2-111 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	2.5	1.2	—	35

Note: *Measuring point = V_{trip}. See Table 2-90 on page 2-166 for a complete table of trip points.

Input Register

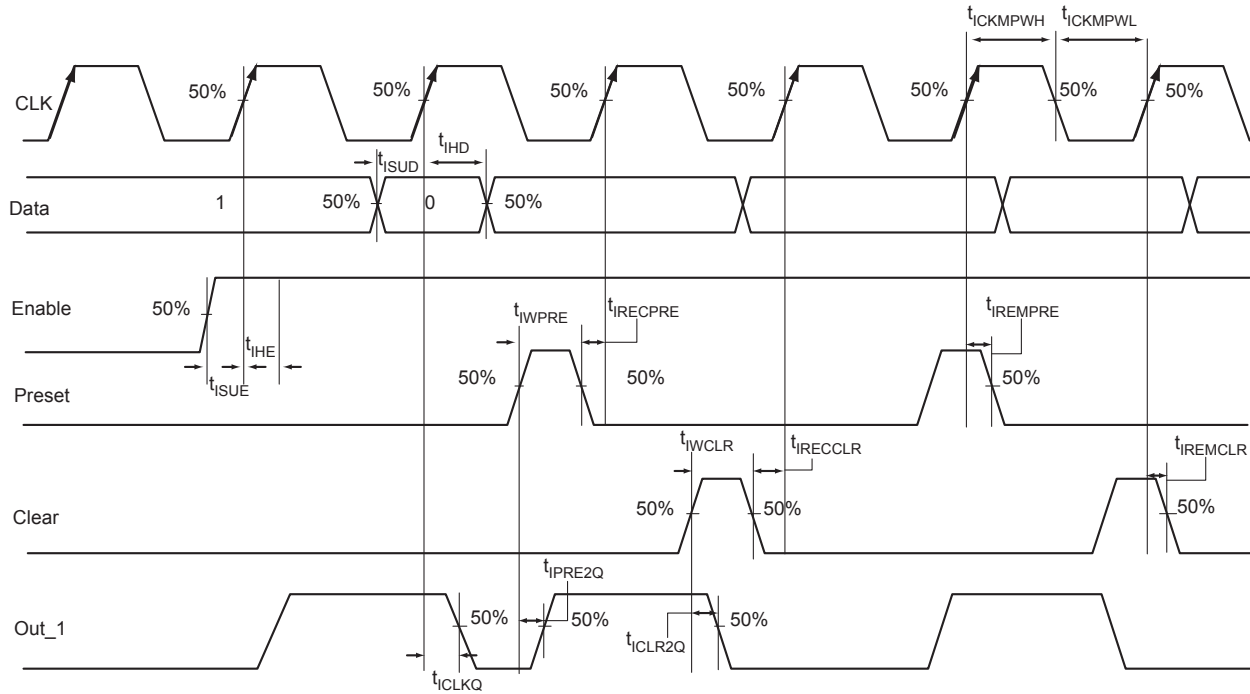


Figure 2-139 • Input Register Timing Diagram

Timing Characteristics

Table 2-176 • Input Data Register Propagation Delays
Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{CLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IREMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Theta-JA

Junction-to-ambient thermal resistance (θ_{JA}) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It should be used with caution but is useful for comparing the thermal performance of one package to another.

A sample calculation showing the maximum power dissipation allowed for the AFS600-FG484 package under forced convection of 1.0 m/s and 75°C ambient temperature is as follows:

$$\text{Maximum Power Allowed} = \frac{T_{J(\text{MAX})} - T_{A(\text{MAX})}}{\theta_{JA}}$$

EQ 4

where

$\theta_{JA} = 19.00^{\circ}\text{C/W}$ (taken from Table 3-6 on page 3-7).

$T_A = 75.00^{\circ}\text{C}$

$$\text{Maximum Power Allowed} = \frac{100.00^{\circ}\text{C} - 75.00^{\circ}\text{C}}{19.00^{\circ}\text{C/W}} = 1.3 \text{ W}$$

EQ 5

The power consumption of a device can be calculated using the Microsemi power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package. If the power consumption is higher than the device's maximum allowable power dissipation, a heat sink can be attached on top of the case, or the airflow inside the system must be increased.

Theta-JB

Junction-to-board thermal resistance (θ_{JB}) measures the ability of the package to dissipate heat from the surface of the chip to the PCB. As defined by the JEDEC (JESD-51) standard, the thermal resistance from junction to board uses an isothermal ring cold plate zone concept. The ring cold plate is simply a means to generate an isothermal boundary condition at the perimeter. The cold plate is mounted on a JEDEC standard board with a minimum distance of 5.0 mm away from the package edge.

Theta-JC

Junction-to-case thermal resistance (θ_{JC}) measures the ability of a device to dissipate heat from the surface of the chip to the top or bottom surface of the package. It is applicable for packages used with external heat sinks. Constant temperature is applied to the surface in consideration and acts as a boundary condition. This only applies to situations where all or nearly all of the heat is dissipated through the surface in consideration.

Calculation for Heat Sink

For example, in a design implemented in an AFS600-FG484 package with 2.5 m/s airflow, the power consumption value using the power calculator is 3.00 W. The user-dependent T_a and T_j are given as follows:

$T_J = 100.00^{\circ}\text{C}$

$T_A = 70.00^{\circ}\text{C}$

From the datasheet:

$\theta_{JA} = 17.00^{\circ}\text{C/W}$

$\theta_{JC} = 8.28^{\circ}\text{C/W}$

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{17.00 \text{ W}} = 1.76 \text{ W}$$

EQ 6

Table 3-8 • AFS1500 Quiescent Supply Current Characteristics (continued)

Parameter	Description	Conditions	Temp.	Min.	Typ.	Max.	Unit
IJTAG	JTAG I/O quiescent current	Operational standby ⁴ , VJTAG = 3.63 V	T _J = 25°C		80	100	μA
			T _J = 85°C		80	100	μA
			T _J = 100°C		80	100	μA
		Standby mode ⁵ or Sleep mode ⁶ , VJTAG = 0 V			0	0	μA
IPP	Programming supply current	Non-programming mode, VPUMP = 3.63 V	T _J = 25°C		39	80	μA
			T _J = 85°C		40	80	μA
			T _J = 100°C		40	80	μA
		Standby mode ⁵ or Sleep mode ⁶ , VPUMP = 0 V			0	0	μA
ICCNVM	Embedded NVM current	Reset asserted, V _{CCNVM} = 1.575 V	T _J = 25°C		50	150	μA
			T _J = 85°C		50	150	μA
			T _J = 100°C		50	150	μA
ICCPLL	1.5 V PLL quiescent current	Operational standby , VCCPLL = 1.575 V	T _J = 25°C		130	200	μA
			T _J = 85°C		130	200	μA
			T _J = 100°C		130	200	μA

Notes:

1. ICC is the 1.5 V power supplies, ICC and ICC15A.
2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.
3. ICCI includes all ICCI0, ICCI1, ICCI2, and ICCI4.
4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.
5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.
6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.

Table 3-11 • AFS090 Quiescent Supply Current Characteristics

Parameter	Description	Conditions	Temp.	Min	Typ	Max	Unit
ICC ¹	1.5 V quiescent current	Operational standby ⁴ , VCC = 1.575 V	T _J = 25°C		5	7.5	mA
			T _J = 85°C		6.5	20	mA
			T _J = 100°C		14	48	mA
		Standby mode ⁵ or Sleep mode ⁶ , V _{CC} = 0 V			0	0	μA
ICC33 ²	3.3 V analog supplies current	Operational standby ⁴ , VCC33 = 3.63 V	T _J = 25°C		9.8	12	mA
			T _J = 85°C		9.8	12	mA
			T _J = 100°C		10.7	15	mA
		Operational standby, only Analog Quad and –3.3 V output ON, VCC33 = 3.63 V	T _J = 25°C		0.30	2	mA
			T _J = 85°C		0.30	2	mA
			T _J = 100°C		0.45	2	mA
		Standby mode ⁵ , VCC33 = 3.63 V	T _J = 25°C		2.9	2.9	mA
			T _J = 85°C		2.9	3.0	mA
			T _J = 100°C		3.5	6	mA
		Sleep mode ⁶ , VCC33 = 3.63 V	T _J = 25°C		17	18	μA
			T _J = 85°C		18	20	μA
			T _J = 100°C		24	25	μA
ICCI ³	I/O quiescent current	Operational standby ⁶ , VCCIx = 3.63 V	T _J = 25°C		260	437	μA
			T _J = 85°C		260	437	μA
			T _J = 100°C		260	437	μA
IJTAG	JTAG I/O quiescent current	Operational standby ⁴ , VJTAG = 3.63 V	T _J = 25°C		80	100	μA
			T _J = 85°C		80	100	μA
			T _J = 100°C		80	100	μA
		Standby mode ⁵ or Sleep mode ⁶ , VJTAG = 0 V			0	0	μA
IPP	Programming supply current	Non-programming mode, VPUMP = 3.63 V	T _J = 25°C		37	80	μA
			T _J = 85°C		37	80	μA
			T _J = 100°C		80	100	μA
		Standby mode ⁵ or Sleep mode ⁶ , VPUMP = 0 V			0	0	μA

Notes:

1. ICC is the 1.5 V power supplies, ICC, ICCPLL, ICC15A, ICCNVM.
2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.
3. ICCI includes all ICCI0, ICCI1, and ICCI2.
4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.
5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.
6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.

FG256				
Pin Number	AFS090 Function	AFS250 Function	AFS600 Function	AFS1500 Function
A1	GND	GND	GND	GND
A2	VCCIB0	VCCIB0	VCCIB0	VCCIB0
A3	GAB0/IO02RSB0V0	GAA0/IO00RSB0V0	GAA0/IO01NDB0V0	GAA0/IO01NDB0V0
A4	GAB1/IO03RSB0V0	GAA1/IO01RSB0V0	GAA1/IO01PDB0V0	GAA1/IO01PDB0V0
A5	GND	GND	GND	GND
A6	IO07RSB0V0	IO11RSB0V0	IO10PDB0V1	IO07PDB0V1
A7	IO10RSB0V0	IO14RSB0V0	IO12PDB0V1	IO13PDB0V2
A8	IO11RSB0V0	IO15RSB0V0	IO12NDB0V1	IO13NDB0V2
A9	IO16RSB0V0	IO24RSB0V0	IO22NDB1V0	IO24NDB1V0
A10	IO17RSB0V0	IO25RSB0V0	IO22PDB1V0	IO24PDB1V0
A11	IO18RSB0V0	IO26RSB0V0	IO24NDB1V1	IO29NDB1V1
A12	GND	GND	GND	GND
A13	GBC0/IO25RSB0V0	GBA0/IO38RSB0V0	GBA0/IO28NDB1V1	GBA0/IO42NDB1V2
A14	GBA0/IO29RSB0V0	IO32RSB0V0	IO29NDB1V1	IO43NDB1V2
A15	VCCIB0	VCCIB0	VCCIB1	VCCIB1
A16	GND	GND	GND	GND
B1	VCOMPLA	VCOMPLA	VCOMPLA	VCOMPLA
B2	VCCPLA	VCCPLA	VCCPLA	VCCPLA
B3	GAA0/IO00RSB0V0	IO07RSB0V0	IO00NDB0V0	IO00NDB0V0
B4	GAA1/IO01RSB0V0	IO06RSB0V0	IO00PDB0V0	IO00PDB0V0
B5	NC	GAB1/IO03RSB0V0	GAB1/IO02PPB0V0	GAB1/IO02PPB0V0
B6	IO06RSB0V0	IO10RSB0V0	IO10NDB0V1	IO07NDB0V1
B7	VCCIB0	VCCIB0	VCCIB0	VCCIB0
B8	IO12RSB0V0	IO16RSB0V0	IO18NDB1V0	IO22NDB1V0
B9	IO13RSB0V0	IO17RSB0V0	IO18PDB1V0	IO22PDB1V0
B10	VCCIB0	VCCIB0	VCCIB1	VCCIB1
B11	IO19RSB0V0	IO27RSB0V0	IO24PDB1V1	IO29PDB1V1
B12	GBB0/IO27RSB0V0	GBC0/IO34RSB0V0	GBC0/IO26NPB1V1	GBC0/IO40NPB1V2
B13	GBC1/IO26RSB0V0	GBA1/IO39RSB0V0	GBA1/IO28PDB1V1	GBA1/IO42PDB1V2
B14	GBA1/IO30RSB0V0	IO33RSB0V0	IO29PDB1V1	IO43PDB1V2
B15	NC	NC	VCCPLB	VCCPLB
B16	NC	NC	VCOMPLB	VCOMPLB
C1	VCCIB3	VCCIB3	VCCIB4	VCCIB4
C2	GND	GND	GND	GND
C3	VCCIB3	VCCIB3	VCCIB4	VCCIB4
C4	NC	NC	VCCIB0	VCCIB0
C5	VCCIB0	VCCIB0	VCCIB0	VCCIB0
C6	GAC1/IO05RSB0V0	GAC1/IO05RSB0V0	GAC1/IO03PDB0V0	GAC1/IO03PDB0V0